

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1962	((magnetic adj random adj access adj memory 'MRAM')) and (conduct\$3 insulat\$3 dielectric magnetic)	USPAT	OR	ON	2005/12/12 09:08
L3	27006	((magnetic near4 memory 'MRAM')) and (conduct\$3 insulat\$3 dielectric magnetic)	USPAT	OR	ON	2005/12/12 09:09
L4	27022	((magnetic near4 memory 'MRAM')) and (conduct\$3 bitline bit adj line insulat\$3 dielectric magnetic)	USPAT	OR	ON	2005/12/12 09:13
L6	27028	((magnetic near4 memory 'MRAM')) and (conduct\$3 bitline bit adj line word adj line wordline insulat\$3 dielectric magnetic)	USPAT	OR	ON	2005/12/12 18:14
L7	1984	((magnetic adj random adj access adj memory 'MRAM')) and (conduct\$3 bitline bit adj line word adj line wordline insulat\$3 dielectric magnetic)	USPAT	OR	ON	2005/12/12 18:15
L8	1176	6 and (magnetic adj random adj access adj memory 'MRAM' conduct\$3 bitline bit adj line word adj line wordline insulat\$3 dielectric magnetic) with barrier	USPAT	OR	ON	2005/12/12 18:18
L9	8	8 and (magnetic adj random adj access adj memory 'MRAM' conduct\$3 bitline bit adj line word adj line wordline insulat\$3 dielectric magnetic) with (polish\$3 near4 stop\$4)	USPAT	OR	ON	2005/12/12 18:13
L10	10	8 and (magnetic adj random adj access adj memory 'MRAM' conduct\$3 bitline bit adj line word adj line wordline insulat\$3 dielectric magnetic) with ((polish\$3 planar\$7) near4 stop\$4)	USPAT	OR	ON	2005/12/12 18:18

L11	27028	((magnetic near4 memory 'MRAM')) and (conduct\$3 bitline bit adj line word adj line wordline insulat\$3 dielectric magnetic)	USPAT	OR	ON	2005/12/12 18:13
L12	1176	11 and (magnetic adj random adj access adj memory 'MRAM' conduct\$3 bitline bit adj line word adj line wordline insulat\$3 dielectric magnetic) with barrier	USPAT	OR	ON	2005/12/12 18:13
L13	7476	((magnetic adj random adj access adj memory 'MRAM')) and (conduct\$3 bitline bit adj line word adj line wordline insulat\$3 dielectric magnetic)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/12/12 18:14
L14	7476	13 and ((magnetic adj random adj access adj memory 'MRAM')) and (conduct\$3 bitline bit adj line word adj line wordline insulat\$3 dielectric magnetic)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/12/12 18:15
L15	798	14 and (magnetic adj random adj access adj memory 'MRAM' conduct\$3 bitline bit adj line word adj line wordline insulat\$3 dielectric magnetic) with barrier	USPAT	OR	ON	2005/12/12 18:16
L16	2044	14 and (magnetic adj random adj access adj memory 'MRAM' conduct\$3 bitline bit adj line word adj line wordline insulat\$3 dielectric magnetic) with barrier	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/12/12 18:16

L17	2044	16 and (magnetic adj random adj access adj memory 'MRAM' conduct\$3 bitline bit adj line word adj line wordline insulat\$3 dielectric magnetic) with barrier	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/12/12 18:18
L18	30	17 and (magnetic adj random adj access adj memory 'MRAM' conduct\$3 bitline bit adj line word adj line wordline insulat\$3 dielectric magnetic) with ((polish\$3 planar\$7) near4 stop\$4)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/12/12 18:19
S2	232	(((magnetic adj random adj access adj memory 'MRAM')) and (conduct\$3 insulat\$3 dielectric magnetic))	USPAT	OR	ON	2005/12/12 08:51
S3	37	(((magnetic adj random adj access adj memory 'MRAM')) and (conduct\$3 insulat\$3 dielectric magnetic)) and (planariz\$4 polish\$3)	USPAT	OR	ON	2002/07/16 16:07
S4	648	(magnetic adj random adj access adj memory 'MRAM')	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2002/07/16 17:45
S5	576	(((magnetic adj random adj access adj memory 'MRAM')) and (conduct\$3 insulat\$3 dielectric magnetic))	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2002/07/16 17:45
S6	262	(((magnetic adj random adj access adj memory 'MRAM')) and (conduct\$3 insulat\$3 dielectric magnetic)) and (groove opening hole via trench)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2002/07/16 17:46

S7	30	((((magnetic adj random adj access adj memory 'MRAM')) and (conduct\$3 insulat\$3 dielectric magnetic)) and (groove opening hole via trench)) and (non adj magnetic nonmagnetic)) and (planariz\$4 polish\$3)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2002/07/16 16:07
S8	115	((((magnetic adj random adj access adj memory 'MRAM')) and (conduct\$3 insulat\$3 dielectric magnetic)) and (groove opening hole via trench)) and (non adj magnetic nonmagnetic)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2002/07/17 09:40
S9	15	MRAM adj device.ti.	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2002/07/16 17:42
S10	1292	magnetic and (pinned adj layer free adj layer)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2002/07/16 17:43
S11	648	(((magnetic adj random adj access adj memory 'MRAM')) and (magnetic adj random adj access adj memory 'MRAM'))	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2002/07/16 17:45
S12	1	"6048739".PN. and (conduct\$3 insulat\$3 dielectric magnetic)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2002/07/16 17:46

S13	576	(((magnetic adj random adj access adj memory 'MRAM')) and (magnetic adj random adj access adj memory 'MRAM')) and (conduct\$3 insulat\$3 dielectric magnetic)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2002/07/16 17:46
S14	262	(((magnetic adj random adj access adj memory 'MRAM')) and (magnetic adj random adj access adj memory 'MRAM')) and (conduct\$3 insulat\$3 dielectric magnetic)) and (groove opening hole via trench)	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2002/07/16 17:46
S15	1	"6153443"	USPAT	OR	ON	2002/07/17 10:26
S16	1	"5569617".PN.	USPAT	OR	OFF	2002/07/17 09:55
S17	1	"5804458".PN.	USPAT	OR	OFF	2002/07/17 09:55
S18	1	"5940319".PN.	USPAT	OR	OFF	2002/07/17 09:56
S19	1	"5768181".PN.	USPAT	OR	OFF	2002/07/17 09:57
S20	1	"5640343".PN.	USPAT	OR	OFF	2002/07/17 09:57
S21	1	"5768181".PN.	USPAT	OR	OFF	2002/07/17 09:59
S22	1	"5329486".PN.	USPAT	OR	OFF	2002/07/17 09:59
S23	1	"5940319".PN.	USPAT	OR	OFF	2002/07/17 09:59
S24	1	"5956267".PN.	USPAT	OR	OFF	2002/07/17 10:00
S25	1	"5768180".PN.	USPAT	OR	OFF	2002/07/17 10:21
S26	1	"5569617".PN.	USPAT	OR	OFF	2002/07/17 10:21
S27	1	"5496759".PN.	USPAT	OR	OFF	2002/07/17 10:21
S28	1	"5064499".PN.	USPAT	OR	OFF	2002/07/17 10:22

S29	1	"5064499".PN.	USPAT	OR	OFF	2002/07/17 10:22
S30	1	"5976713".PN.	USPAT	OR	OFF	2002/07/17 10:24
S31	1	"5956267".PN.	USPAT	OR	OFF	2002/07/17 10:24
S41	14	"5970373"	USPAT	OR	ON	2005/03/15 12:41